INTEGRATED CIRCUITS

DATA SHEET

74LV00Quad 2-input NAND gate

Product specification
Supersedes data of 1998 Apr 13
IC24 Data Handbook





Quad 2-input NAND gate

74LV00

FEATURES

• Wide operating voltage: 1.0 to 5.5 V

Optimized for low voltage applications: 1.0 to 3.6 V

Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V

 Typical V_{OLP} (output ground bounce) < 0.8 V at V_{CC} = 3.3 V, $T_{amb} = 25^{\circ}C$

 Typical V_{OHV} (output V_{OH} undershoot) > 2 V at V_{CC} = 3.3 V, $T_{amb} = 25^{\circ}C$

Output capability: standard

I_{CC} category: SSI

DESCRIPTION

The 74LV00 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC/HCT00.

The 74LV00 provides the 2-input NAND function.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25^{\circ}C$; $t_r = t_f \le 2.5 \text{ ns}$

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PHL} /t _{PLH}	Propagation delay nA, nB to nY	$C_L = 15 \text{ pF};$ $V_{CC} = 3.3 \text{ V}$	7	ns
C _I	Input capacitance		3.5	pF
C _{PD}	Power dissipation capacitance per gate	See Notes 1 and 2	22	pF

NOTES:

 C_{PD} is used to determine the dynamic power dissipation (P_D in μW)

P_D = C_{PD} × V_{CC}² × f_i + \(\sum_{i} \) (C_L × V_{CC}² × f_o) where:

f_i = input frequency in MHz; C_L = output load capacitance in pF;

f_o = output frequency in MHz; V_{CC} = supply voltage in V;

\(\sum_{i} \) (C_L × V_{CC}² × f_o) = sum of the outputs.

2. The condition is V_I = GND to V_{CC}.

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
14-Pin Plastic DIL	-40°C to +125°C	74LV00 N	74LV00 N	SOT27-1
14-Pin Plastic SO	-40°C to +125°C	74LV00 D	74LV00 D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +125°C	74LV00 DB	74LV00 DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +125°C	74LV00 PW	74LV00PW DH	SOT402-1

PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1, 4, 9, 12	1A – 4A	Data inputs
2, 5, 10, 13	1B – 4B	Data inputs
3, 6, 8, 11	1Y – 4Y	Data outputs
7	GND	Ground (0 V)
14	V _{CC}	Positive supply voltage

FUNCTION TABLE

INP	JTS	OUTPUTS
nA	nY	
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

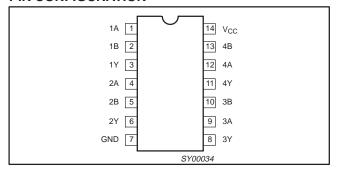
NOTES:

H = HIGH voltage level L = LOW voltage level

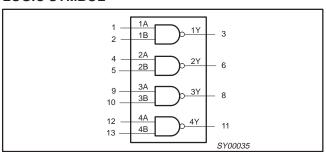
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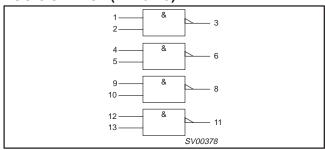
PIN CONFIGURATION



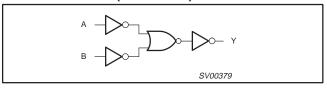
LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)



LOGIC DIAGRAM (ONE GATE)



RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CC}	DC supply voltage	See Note 1	1.0	3.3	5.5	V
VI	Input voltage		0	_	V _{CC}	V
Vo	Output voltage		0	_	V _{CC}	V
T _{amb}	Operating ambient temperature range in free air	See DC and AC characteristics	-40 -40		+85 +125	°C
t _r , t _f	Input rise and fall times	$V_{CC} = 1.0V \text{ to } 2.0V$ $V_{CC} = 2.0V \text{ to } 2.7V$ $V_{CC} = 2.7V \text{ to } 3.6V$ $V_{CC} = 3.6V \text{ to } 5.5V$	- - -	- - - -	500 200 100 50	ns/V

NOTE:

1. The LV is guaranteed to function down to $V_{CC} = 1.0V$ (input levels GND or V_{CC}); DC characteristics are guaranteed from $V_{CC} = 1.2V$ to $V_{CC} = 5.5V$.

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ABSOLUTE MAXIMUM RATINGS^{1, 2}

In accordance with the Absolute Maximum Rating System (IEC 134). Voltages are referenced to GND (ground = 0V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
±I _{IK}	DC input diode current	$V_I < -0.5 \text{ or } V_I > V_{CC} + 0.5V$	20	mA
±loĸ	DC output diode current	$V_{O} < -0.5 \text{ or } V_{O} > V_{CC} + 0.5 V$	50	mA
±ΙΟ	DC output source or sink current – standard outputs	$-0.5V < V_O < V_{CC} + 0.5V$	25	mA
±I _{GND} , ±I _{CC}	DC V _{CC} or GND current for types with – standard outputs		50	mA
T _{stg}	Storage temperature range		-65 to +150	°C
P _{TOT}	Power dissipation per package – plastic DIL – plastic mini-pack (SO) – plastic shrink mini-pack (SSOP and TSSOP)	for temperature range: -40 to +125°C above +70°C derate linearly with 12 mW/K above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	750 500 400	mW

NOTES:

DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0V).

					LIMITS			
SYMBOL	PARAMETER	TEST CONDITIONS	-40	°C to +8	5°C	-40°C to	+125°C	UNIT
			MIN	TYP ¹	MAX	MIN	MAX	
		V _{CC} = 1.2V	0.9			0.9		
\/	HIGH level Input	V _{CC} = 2.0V	1.4			1.4] _{\/}
V_{IH}	voltage	V _{CC} = 2.7 to 3.6V	2.0			2.0		1 °
		V _{CC} = 4.5 to 5.5V	0.7*V _{CC}			0.7*V _{CC}		1
		V _{CC} = 1.2V			0.3		0.3	
VII	LOW level Input	V _{CC} = 2.0V			0.6		0.6	
VIL	voltage	V _{CC} = 2.7 to 3.6V			0.8		0.8	1
		V _{CC} = 4.5 to 5.5			0.3*V _{CC}		0.3*V _{CC}	1
		$V_{CC} = 1.2V; V_I = V_{IH} \text{ or } V_{IL;} -I_O = 100 \mu A$		1.2				
	l <u>.</u>	$V_{CC} = 2.0V$; $V_I = V_{IH}$ or V_{IL} ; $-I_O = 100\mu A$	1.8	2.0		1.8		1
V_{OH}	HIGH level output voltage; all outputs	$V_{CC} = 2.7V$; $V_I = V_{IH}$ or V_{IL} ; $-I_O = 100\mu A$	2.5	2.7		2.5		V
	Voltage, all outputs	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL}; -I_O = 100 \mu A$	2.8	3.0		2.8		1
		$V_{CC} = 4.5V; V_I = V_{IH} \text{ or } V_{IL;} -I_O = 100 \mu A$	4.3	4.5		4.3		1
Voh	HIGH level output voltage;	$V_{CC} = 3.0V$; $V_I = V_{IH}$ or V_{IL} ; $-I_O = 6$ mA	2.40	2.82		2.20		
VОН	STANDARD outputs	$V_{CC} = 4.5V$; $V_I = V_{IH}$ or V_{IL} ; $-I_O = 12mA$	3.60	4.20		3.50] `
		$V_{CC} = 1.2V; V_I = V_{IH} \text{ or } V_{IL;} I_O = 100 \mu A$		0				
	L OW level solved	$V_{CC} = 2.0V; V_I = V_{IH} \text{ or } V_{IL;} I_O = 100 \mu A$		0	0.2		0.2]
V_{OL}	LOW level output voltage; all outputs	$V_{CC} = 2.7V; V_I = V_{IH} \text{ or } V_{IL;} I_O = 100 \mu A$		0	0.2		0.2	V
	l voltago, all outputo	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} I_O = 100 \mu A$		0	0.2		0.2	1
		$V_{CC} = 4.5V; V_I = V_{IH} \text{ or } V_{IL;} I_O = 100 \mu A$		0	0.2		0.2	1
V _{OL}	LOW level output voltage;	$V_{CC} = 3.0V$; $V_I = V_{IH}$ or V_{IL} ; $I_O = 6mA$		0.25	0.40		0.50	
▼OL	STANDARD outputs	$V_{CC} = 4.5V$; $V_I = V_{IH}$ or V_{IL} ; $I_O = 12mA$		0.35	0.55		0.65	

^{1.} Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

^{2.} The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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DC ELECTRICAL CHARACTERISTICS (Continued)

Over recommended operating conditions. Voltages are referenced to GND (ground = 0V).

					LIMITS			
SYMBOL	PARAMETER	TEST CONDITIONS	-40	°C to +85	5°C	-40°C to	UNIT	
			MIN	TYP ¹	MAX	MIN	MAX	
l _l	Input leakage current	$V_{CC} = 5.5V$; $V_I = V_{CC}$ or GND			1.0		1.0	μА
Icc	Quiescent supply current; SSI	$V_{CC} = 5.5V$; $V_{I} = V_{CC}$ or GND; $I_{O} = 0$			20.0		40	μА
Δl _{CC}	Additional quiescent supply current	$V_{CC} = 2.7V$ to 3.6V; $V_I = V_{CC} - 0.6V$			500		850	μА

NOTE:

AC CHARACTERISTICS

GND = 0V; $t_r = t_f \le 2.5 \text{ns}$; $C_L = 50 \text{pF}$; $R_L = 1 \text{K}\Omega$

			CONDITION			LIMITS				
SYMBOL	PARAMETER	WAVEFORM	CONDITION		40 to +85 °	С	–40 to ₁	UNIT		
			V _{CC} (V)	MIN	TYP ¹	MAX	MIN	MAX		
			1.2		45					
		Figures 1, 2	Figures 1, 2	2.0		15	26		31	
t _{PHL/PLH}	Propagation delay nA, nB to nY			2.7		11	18		23	ns
	,		3.0 to 3.6		9 ²	15		18		
			4.5 to 5.5		6.5 ³	11		14		

NOTES:

- 1. Unless otherwise stated, all typical values are measured at $T_{amb} = 25$ °C.
- 2. Typical values are measured at V_{CC} = 3.3 V.
- 3. Typical values are measured at $V_{CC} = 5.0 \text{ V}$.

AC WAVEFORMS

 V_M = 1.5 V at $V_{CC} \geq$ 2.7 V and \leq 3.6 V;

 $V_M = 0.5 \times V_{CC}$ at $V_{CC} < 2.7$ V and ≥ 4.5 V;

 $\mbox{V}_{\mbox{OL}}$ and $\mbox{V}_{\mbox{OH}}$ are the typical output voltage drop that occur with the output load.

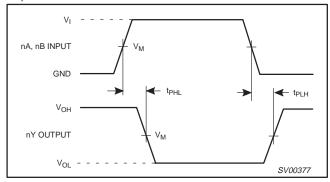


Figure 1. Input (nA, nB) to output (nY) propagation delays.

TEST CIRCUIT

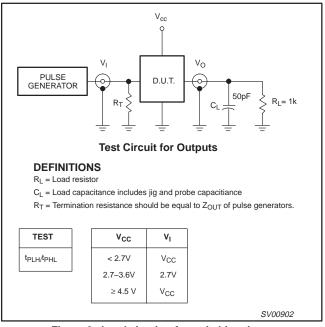


Figure 2. Load circuitry for switching times.

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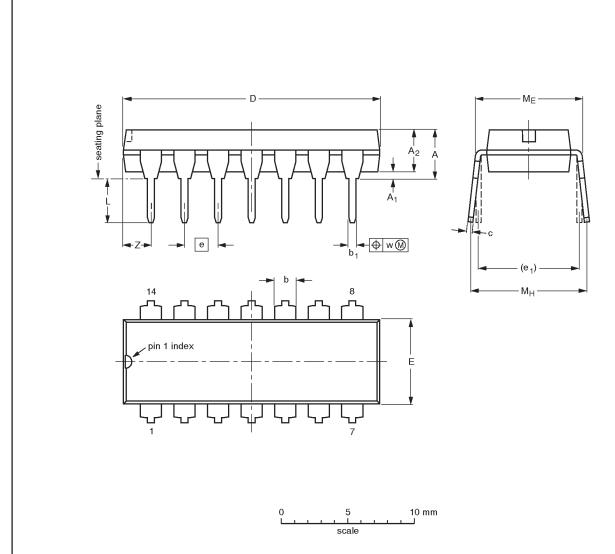
^{1.} All typical values are measured at $T_{amb} = 25$ °C.

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DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	ı
SOT27-1	050G04	MO-001AA			92-11-17 95-03-11	

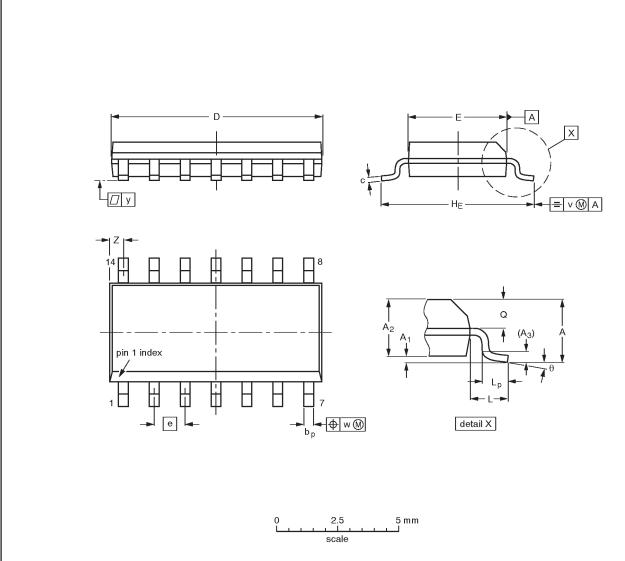
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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	Α1	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.0098 0.0039		0.01		0.0098 0.0075	0.35 0.34	0.16 0.15	0.050	0.24 0.23	0.041		0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT108-1	076E06\$	MS-012AB				91-08-13 95-01-23	

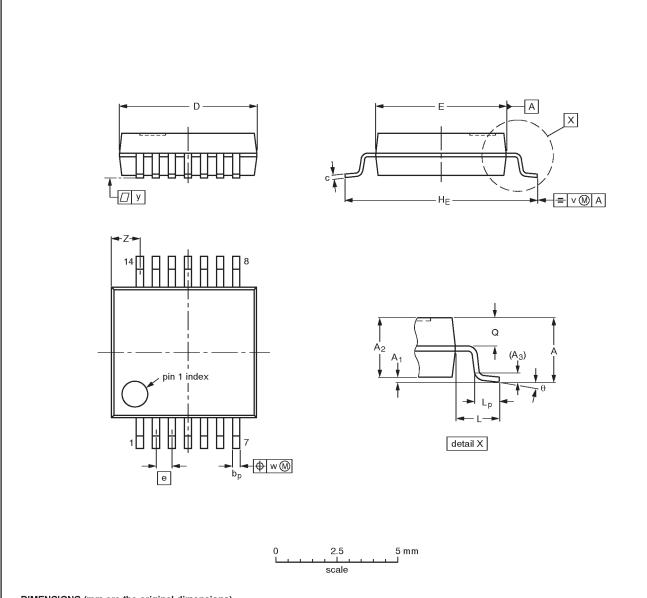
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Quad 2-input NAND gate

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	bp	C	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Ø	٧	w	у	Z ⁽¹⁾	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

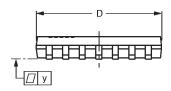
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1990E DATE	
SOT337-1		MO-150AB				-95-02-04 96-01-18	

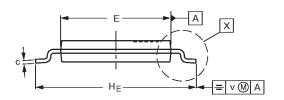
Quad 2-input NAND gate

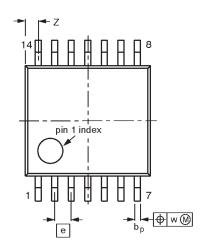
74LV00

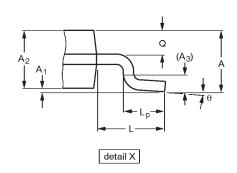
TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1











DIMENSIONS (mm are the original dimensions)

UNIT	A max.	Α1	A ₂	A ₃	bр	c	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				-94-07-12 95-04-04	

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	DEFINITIONS							
Data Sheet Identification	Product Status	Definition						
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specificati may change in any manner without notice.						
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.						
Product Specification	Full Production	This data sheet contains Final Specifications. Philips Semiconductors reserves the right to make changes at any time without notice, in order to improve design and supply the best possible product.						

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